NSN 5962-01-208-1259

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View Online at https://aerobasegroup.com/nsn/5962-01-208-1259 **Body Length:** 1.290 inches **Body Width:** Between 0.500 inches and 0.610 inches **Body Height:** 0.210 inches **Maximum Power Dissipation Rating:** 1.02 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Communications control center an/tsq-111 **Features Provided:** Hermetically sealed and burn in and 3-state output and w/active pull-up and w/enable and programmable and electrostatic sensitive **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 13 input **Case Outline Source And Designator:** D-3 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 7.0 volts power source **Time Rating Per Chacteristic:** 90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:**

Rom

Memory Capacity:

Unknown

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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